

Attorney Docket #: N1085-00018(TSMC2002-0629)
Application Serial No.: 10/730,533
TC/AU No.: 1756
Amendment dated March 8, 2007

Please amend the Abstract as follows:

A chromeless phase shifting mask comprises a mask substrate and at least one annular equal line space phase shifting pattern on the mask substrate to produce [[a]] an substantially unexposed region on a semiconductor substrate. A method of manufacturing a chromeless phase shifting mask comprises providing a mask substrate; forming a layer of resist material on said the mask substrate; patterning the resist layer; patterning at least one annular equal line space phase shifting pattern on patterning at least one annular equal line space phase shifting pattern on the resist layer; patterning the resist layer pattern onto said the mask substrate; and removing a remaining portion of said the resist layer. A method of transferring a pattern onto a semiconductor substrate comprises illuminating a mask comprising at least one annular equal line space phase shifting pattern on the mask to produce a substantially unexposed region on a semiconductor substrate.